

Abstract of the Disclosure

The present invention relates to a method for forming a storage node contact of a semiconductor device. The method includes the steps of: depositing sequentially a conductive layer, a nitride layer and a polysilicon layer on a substrate having an insulating structure and a conductive structure; etching selectively the polysilicon layer, the nitride layer and the conductive layer to form a plurality of conductive patterns with a stack structure of the conductive layer and a dual hard mask including the polysilicon layer and the nitride layer; forming an insulation layer along a profile containing the conductive patterns; and etching the insulation layer by using a line type photoresist pattern as an etch mask to form a contact hole exposing the conductive structure disposed between the neighboring conductive patterns.